rfmd.com

Gan WIDE-BAND POWER AMPLIFIER

RoHS Compliant & Pb-Free Product Package Style: Flanged Ceramic

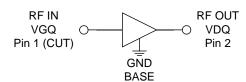


Features

- Peak Power=30W
- Gain=14dB
- Advanced GaN HEMT Technology
- 48V Operation
- Optimized Evaluation Board Layout for 50Ω Operation

Applications

- Commercial Wireless Infrastructure
- Cellular and WiMAX Infrastructure
- General Purpose Broadband **Amplifiers**
- Public Mobile Radios
- Industrial. Scientific and Medical



Functional Block Diagram

Product Description

The RF3931 is designed for commercial infrastructure, cellular and WiMAX infrastructure and general purpose broadband amplifier applications. Using an advanced high power density Gallium Nitride (GaN) semiconductor process, these high-performance amplifiers achieve high efficiency and flat gain over a broad frequency range in a single amplifier design. The RF3931 is an unmatched GaN transistor packaged in a flanged ceramic package which provides excellent thermal stability through the use of advanced heat sink and power dissipation technologies. Ease of integration is accomplished through the incorporation of simple, optimized matching networks external to the package that provide wideband gain and power performance in a single amplifier.

Ordering Information

RF3931 GaN Wide-Band Power Amplifier

Optimum Technology Matching® Applied

☐ GaAs HBT	☐ SiGe BiCMOS	□ GaAs pHEMT	
☐ GaAs MESFET	☐ Si BiCMOS	☐ Si CMOS	
☐ InGaP HBT	☐ SiGe HBT	☐ Si BJT	

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Please contact RFMD Technical Support at (336) 678-5570 for more information.